

/ Descriptions

Silicon PNP transistor in a TO-220 Plastic Package.

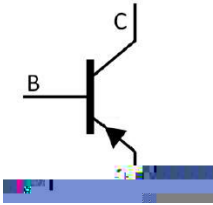
/ Features

Complement to KSD288.

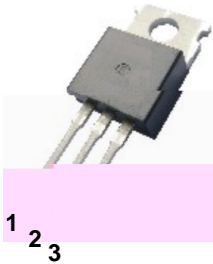
/ Applications

Low frequency power amplifier.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

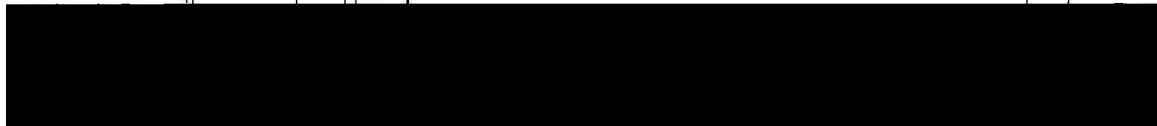
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	R	O	Y
h_{FE} Range	40 80	70 140	120 240

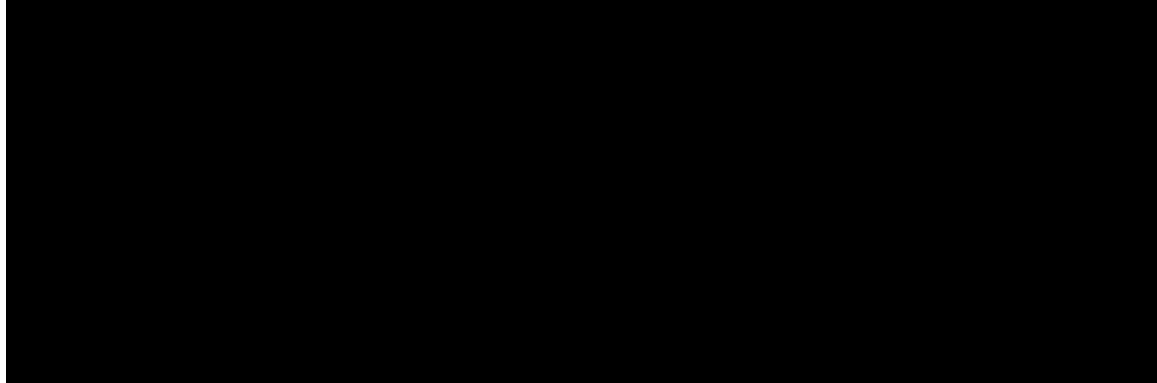
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-55	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-3.0	A
Collector Power Dissipation	P_C	2.0	W
	$P_C(T_C=25 \text{ }^\circ\text{C})$	25	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter Symbol

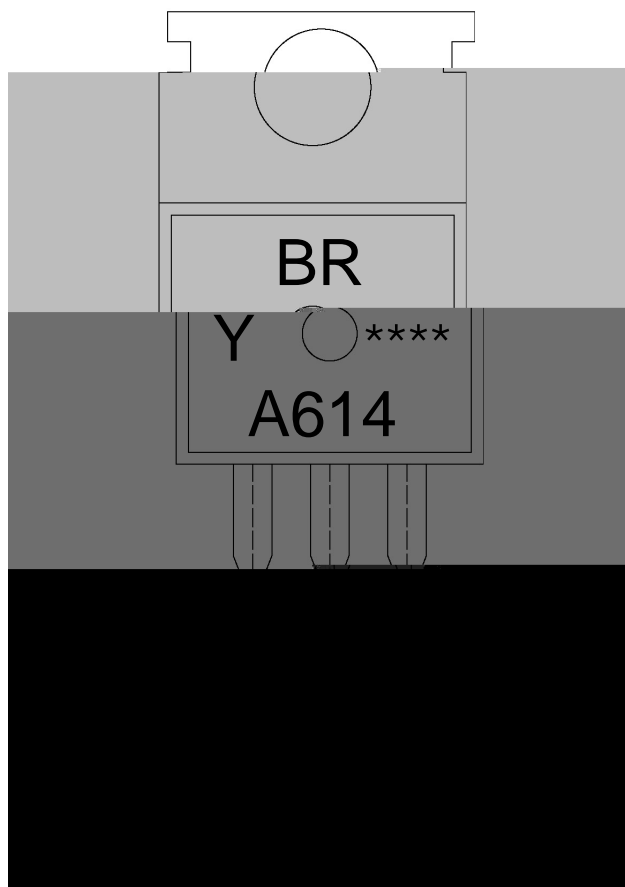
/ Package Dimensions



Dimensions in millimeters



/ Marking Instructions



Note:

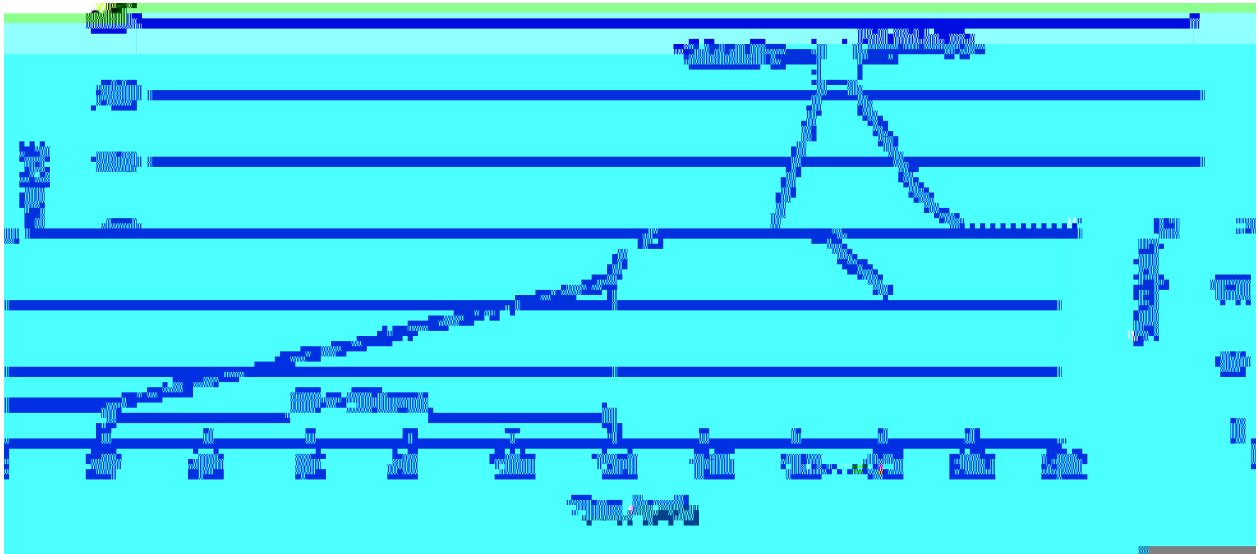
BR: Company Code

A614: Product Type.

Y: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



- | | | | | | | |
|---|-----|-----|----|----------|---|--------------------------------------|
| 1 | 25 | 150 | 60 | 90sec; | Note: | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255 | 5 | 5 | 0.5sec; | 2.Peak Temp.:255 5 , Duration:5 0.5sec. | |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. | |

/ Resistance to Soldering Heat Test Conditions

270 5 10 1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units		Dimension	(unit mm ³)
	Units/Bag	Bags/Inner Box		
		Units/Inner Box	Innener4,2xnsOuteere4,2	